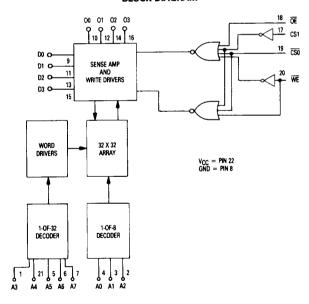
TTL 256 x 4-Bit Random Access Memory

The 93422 Series are 1024-bit Read/Write RAMs, organized 256 words by 4 bits, designed for high performance main memory and control storage applications.

They have full decoding on-chip, separate data input and data output lines, an active low-output enable, write enable, and two chip selects, one active high, one active low. These memories are fully compatible with standard TTL logic families. A three-state output is provided to drive bus-organized systems and/or highly capacitive loads.

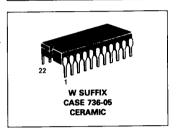
- Three-State Outputs
- Non-Inverting Data Outputs
- Power Dissipation 0.26 mW/Bit Typical
- Standard 22-Pin, 400 Mil Wide Package
- Power Dissipation Decreases with Increasing Temperature
- Organized 256 Words x 4 Bits
- Two Chip Select Lines for Memory Expansion
- Address Access Time: 93422 60 ns Max
 93L422A 55 ns Max
 93L422 75 ns Max

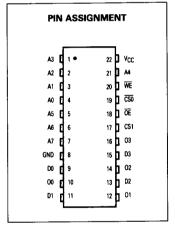
BLOCK DIAGRAM



Military 93422 93L422.A







PIN NAMES					
CS0, CS1	. Chip Selects				
A0-A7	Address Inputs				
ŌĒ					
WE	. Write Enable				
D0-D3					
00-03	. Data Outputs				

FUNCTIONAL DESCRIPTION

The 93422 Series are fully decoded 1024-bit random access memories organized 256 words by 4 bits. Word selections are achieved by means of an 8-bit address, A0-A7.

The Chip Select (CS0 and CS1) inputs provide for memory array expansion. For large memories, the fast chip select time permits the decoding of chip select from the address without increasing address access time.

The read and write operations are controlled by the state of the active low Write Enable (WE, Pin 20). With WE and CS0 held low and the CS1 held high, the data at D_{Π} is written into the addressed location. To read, WE and CS1 are held high and CS0 is held low. Data in the specified location is presented at the output (00–02) and is non-inverted.

The three-state outputs provide drive capability for higher speeds with capacitive load systems. The third state (high impedance) allows bus-organized systems where multiple outputs are connected to a common bus.

During writing, the output is held in a high-impedance state.

GUARANTEED OPERATING RANGES

	Suppl	Ambient			
Part Number	Min	Nom	Max	Temp. (T _A)	
93422/BWAJC 93L422/BWAJC 93L422A/BWAJC	4.5 V	5.0 V	5.5 V	−55°C to +125°C	

ABSOLUTE MAXIMUM RATINGS*

Input Current (dc)	- 12 mA to +5.0 mA
Output Current (dc) (Output Low)	+ 20 mA
Voltage Applied to Outputs (Output High)	-0.5 V to +5.5 V
Input Voltage (dc)	-0.5 V to +5.5 V
V _{CC} Pin Potential to Ground Pin	-0.5 V to +7.0 V
Operating Junction Temperature, T _J Ceramic Package (W Suffix)	<165℃
Storage Temperature Ceramic Package (W Suffix)	-65°C to +150°C

^{*}Device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded.

TRUTH TABLE

		Inputs				
ŌĒ	CS0	CS1	WE	D0-D3	O0-O3	Mode
Х	Н	х	Х	х	High Z	Not Selected
X	X	L	Х	Х	High Z	Not Selected
X	L	Н	L	L	High Z	Write "0"
Х	L	н	L	н	High Z	Write "1"
Н	Х	Х	X	х	High Z	Output Disabled
L	L	Н	Н	X	00-03	Read

H = High Voltage Level

DC OPERATING CONDITIONS AND CHARACTERISTICS

(Full operating voltage and temperature range)

	Limits								
Symbol	Characteristic		Characteristic		Min	Max	Units	Cond	itions
VOL	Output Low Voltage		_	0.45	Vdc	V _{CC} = Min, I _{OL} = 8.0	mA		
VIH	Input High Voltage		2.1	_	Vdc	Guaranteed Input High Voltage for All Inpu			
VIL	Input Low Voltage			0.8	Vdc	Guaranteed Input Low	Voltage for All Inputs		
IIL	Input Low Current		0.01	- 300	μAdc	V _{CC} = Max, V _{in} = 0.45 V			
ļш	Input High Current		_	40	μAdc	V _{CC} = Max, V _{in} = 5.5 V			
l _{off}	Output Current (High Z)		_	50 - 50	μAdc	V _{CC} = Max, V _{out} = 2.4 V V _{CC} = Max, V _{out} = 0.45 V			
los	Output Current Short Circuit to Ground		- 10	70	mAdc	V _{CC} = Max (Note 1)			
Voн	Output High Voltage		2.4	_	Vdc	V _{CC} = Min, I _{OH} = -5.2 mA			
VIK	Input Diode Clamp Volta	ge	_	- 1.5	Vdc	V _{CC} = Max, I _{in} = -10 mA			
		93422	_	130	mAdc	T _A = +125°C			
				155	mAdc	T _A = +25°C			
ICC Power Supply Current		—	170	mAdc	T _A = -55°C	Vcc = 5.5 V,			
lcc	Tower Supply Current	93L422A	_	70	mAdc	T _A = +125°C	All Inputs Grounded		
	93L422		_	80	mAdc	T _A = +25°C	1		
			_	90	mAdc	T _A = -55°C	1		

L = Low Voltage Level
X = Don't Care (High or Low)

AC OPERATING CONDITIONS AND CHARACTERISTICS

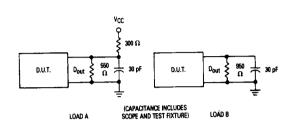
(Full operating voltage and temperature range)

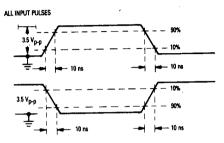
AC TEST LOAD AND WAVEFORMS

LOADING CONDITIONS

ù.

INPUT PULSES





	Characteristic	93422/	93422/BWAJC		93L422/BWAJC		93L422A/BWAJC	
Symbol	(Notes 1, 2, 3, 4, 5)	Min	Max	Min	Max	Min	Max	Unit
READ MODE	DELAY TIMES							ns
tACS	Chip Select Time	—	45		45	-	40	
TZRCS	Chip Select to High Z	-	45	1 - 1	45	-	40	
tAOS	Output Enable Time	I —	45		45	_	40	
¹ZROS	Output Enable to High Z	l –	45		45	_	40	
tAA	Address Access Time		60		75		55	
WRITE MODE	DELAY TIMES					ľ		ns
tzws	Write Disable to High Z	l –	45	-	45	l –	45	
twr	Write Recovery Time		50		50		45	
	INPUT TIMING REQUIREMENTS					1		ns
₩	Write Pulse Width (to guarantee write)	30	_	30	_	40	_	
*WSD	Data Setup Time Prior to Write	5.0	_	5.0	_	5.0	-	
tWHD	Data Hold Time After Write	5.0	_	5.0		5.0	_	
tWSA	Address Setup Time (at tw = Min)	10	_	10	_	10	-	
tWHA	Address Hold Time	10	-	10		5.0	-	
twscs	Chip Select Setup Time	5.0		5.0	_	5.0	-	
twics	Chip Select Hold Time	5.0		5.0	<u> </u>	5.0		L

NOTES:

IOTES:
1. Output short circuit conditions must not exceed 1.0 second duration.
2. The maximum address access time is guaranteed to be the worst-case bit in the memory.
3. Load A used to measure transitions between logic levels and from High Z state to logic Low state.

Load B used to measure transitions between High Z state to logic High state.

Load C used to measure transitions from either logic High or Low state to High Z state.

4. All time measurements are referenced to + 1.5 Vdc except transitions into the High Z state where outputs are referenced to a delta of 0.5 Vdc from the logic level using load C.

from the logic level using Load C.

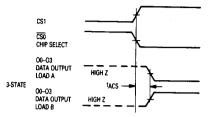
5. See test circuit and waveforms.

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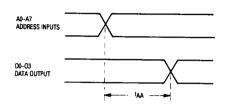
READ OPERATION TIMING DIAGRAM

(All Time Measurements Referenced to 1.5 V)

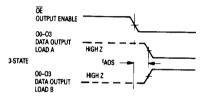
PROPAGATION DELAY FROM CHIP SELECT



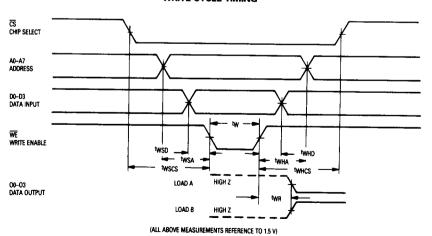
PROPAGATION DELAY FROM ADDRESS INPUTS



PROPAGATION DELAY FROM OUTPUT ENABLE

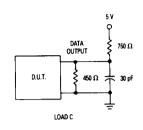


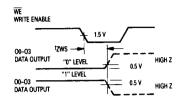
WRITE CYCLE TIMING



MOTOROLA MEMORY DATA

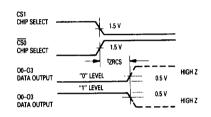
WRITE ENABLE TO HIGH Z DELAY

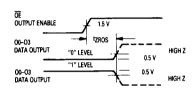




PROPAGATION DELAY FROM CHIP SELECT TO HIGH Z

PROPAGATION DELAY FROM OUTPUT ENABLE TO HIGH Z





(ALL IZXXX PARAMETERS ARE MEASURED AT A DELTA OF 0.5 V FROM THE LOGIC LEVEL AND USING LOAD C.)

	θ _{JA} (Jui Amb	nction to lient)	
Package	Blown*	Still	$\theta_{ m JC}$ (Junction to Case)
W Suffix	50°C/W	75°C/W	15°C/W

^{*500} linear ft. per minute blown air.

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